

<b>L Number</b>	<b>Hits</b>	<b>Search Text</b>	<b>DB</b>	<b>Time stamp</b>
<b>1</b>	<b>0</b>	<b>219/210,219,521</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2003/05/12 09:52</b>
<b>2</b>	<b>2653</b>	<b>219/210 or 219/219 or 219/521</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2003/05/12 10:27</b>
<b>3</b>	<b>156</b>	<b>(219/210 or 219/219 or 219/521) and transistor</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2003/05/12 09:54</b>
<b>4</b>	<b>51</b>	<b>((219/210 or 219/219 or 219/521) and transistor) and semiconductor</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2003/05/12 09:54</b>
<b>7</b>	<b>0</b>	<b>((((219/210 or 219/219 or 219/521) and transistor) and semiconductor) and heated adj object</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2003/05/12 09:55</b>
<b>8</b>	<b>1</b>	<b>((((219/210 or 219/219 or 219/521) and transistor) and semiconductor) and heated adj chamber</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2003/05/12 11:17</b>
<b>10</b>	<b>0</b>	<b>((((219/210 or 219/219 or 219/521) and transistor) and semiconductor) and heated) and drain adj region adj region</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2003/05/12 10:07</b>
<b>9</b>	<b>1</b>	<b>((((219/210 or 219/219 or 219/521) and transistor) and semiconductor) and heated) and source adj region</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2003/05/12 12:05</b>
<b>12</b>	<b>0</b>	<b>((((219/210 or 219/219 or 219/521) and transistor) and semiconductor) and heated) and channel adj region</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2003/05/12 10:07</b>
<b>13</b>	<b>0</b>	<b>((((219/210 or 219/219 or 219/521) and transistor) and semiconductor) and heat\$3) and channel adj region</b>	<b>USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB</b>	<b>2003/05/12 12:06</b>

14	0	((219/210 or 219/219 or 219/521) and transistor) and semiconductor) and channel adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 10:11
15	0	((219/210 or 219/219 or 219/521) and transistor) and channel adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 10:12
16	0	(219/210 or 219/219 or 219/521) and channel adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 10:12
11	1	((219/210 or 219/219 or 219/521) and transistor) and semiconductor) and heated) and drain adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 10:18
6	37	((219/210 or 219/219 or 219/521) and transistor) and semiconductor) and heated	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 12:03
17	1961	219/210 and 219/219 and 219/521	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 10:28
18	0	219/210 and 219/219 and 219/521	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 10:28
5	48	((219/210 or 219/219 or 219/521) and transistor) and semiconductor) and heat\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 10:29
19	3	((219/210 or 219/219 or 219/521) and transistor) and heated adj chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 11:19
20	15	(219/210 or 219/219 or 219/521) and heated adj chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 11:22

21	374	semiconductor and heated adj chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 11:23
22	73	(semiconductor and heated adj chamber) and transistor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 11:23
24	3	((semiconductor and heated adj chamber) and transistor) and circuit) and 219/\$.cccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 11:42
23	61	((semiconductor and heated adj chamber) and transistor) and circuit	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 12:16
26	36922	"5243212" and dielectric layer with window	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 11:39
27	0	"5243212" and dielectric adj layer with window	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 11:40
28	0	"5243212" and dielectric adj layer same window	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 11:40
29	716	transistor and dielectric adj layer with window	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 11:41
30	655	(transistor and dielectric adj layer with window) and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 11:42
31	534	((transistor and dielectric adj layer with window) and semiconductor) and circuit	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 11:42

32	0	(((transistor and dielectric adj layer with window) and semiconductor) and circuit) and 219/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 11:43
33	406	(((transistor and dielectric adj layer with window) and semiconductor) and circuit) and 257/\$.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 11:44
34	9	(((transistor and dielectric adj layer with window) and semiconductor) and circuit) and 257/344	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 11:45
25	13	"5243212"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 11:59
35	27	"4888624"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 12:03
38	1	"4888624" and channel adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 12:06
36	7	(((transistor and dielectric adj layer with window) and semiconductor) and circuit) and 257/344) and source adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 12:12
37	5	(((transistor and dielectric adj layer with window) and semiconductor) and circuit) and 257/344) and channel adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 12:08
39	7	(((transistor and dielectric adj layer with window) and semiconductor) and circuit) and 257/344) and drain adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 12:08
40	6	(((transistor and dielectric adj layer with window) and semiconductor) and circuit) and 257/344) and gate adj electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 12:13

41	0	(((semiconductor and heated adj chamber) and transistor) and circuit) and insulat\$3 adj2 barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 12:17
42	0	(((semiconductor and heated adj chamber) and transistor) and circuit) and insulat\$3 adj2 barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 12:17
43	15	(((semiconductor and heated adj chamber) and transistor) and circuit) and insulat\$3 with barrier	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 12:21
44	0	(((semiconductor and heated adj chamber) and transistor) and circuit) and insulat\$3 with barrier with channel adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 12:22
45	0	(((semiconductor and heated adj chamber) and transistor) and circuit) and insulat\$3 with barrier same channel adj region	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/05/12 12:22